

DESCRIPTION

The FMMT491 are available in SOT-23 package

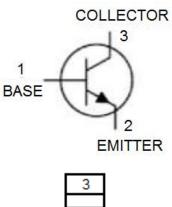
FEATURES

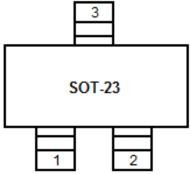
- Low Saturation
- Complementary to FMMT591
- Excellent h_{FE} Linearity
- Available in SOT-23 package

ORDERING INFORMATION

Package Type	Part Number	
SOT-23	FMMT491	
Note	SPQ:3,000pcs/Reel	
AiT provides all RoHS Compliant Products		

PIN DESCRIPTION





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ABSOLUTE MAXIMUM RATINGS

V _{CBO} , Collector-Base Voltage	80V
V _{CEO} , Collector-Emitter Voltage	60V
V _{EBO} , Emitter-Base Voltage	5V
I _C , Collector Current-Continuous	1000mA
Pc, Collector Dissipation	500mW
T _J , T _{STG} , Junction and Storage Temperature	-55°C ~150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

T_A=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	80	-	1	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 10mA, I _B =0	60	-	ı	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =100μA,I _C =0	5	-	-	V
Collector Cut-off Current	Ісво	V _{CB} =60V, I _E =0	-	-	0.1	uA
Emitter Cut-off Current	I _{EBO}	V _{EB} =4V, I _C =0	1	-	0.1	uA
DC Current Gain	hfE	V _{CE} =5V, I _C =1mA	100	-	-	
		V _{CE} =5V, I _C =500mA	100	-	300	
		V _{CE} =5V, I _C =1A	80	-	-	
		V _{CE} =5V, I _C =2A	30	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA	-	-	0.25	V
		I _C =1A, I _B =100mA			0.5	
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1A, I _B =100mA	-	-	1.1	V
Transition Frequency	f⊤	V _{CE} =10V, I _C =50mA	150	-	-	N 41 1
		f=100MHz				MHz
Collector Output Capacitance	Cob	V _{CB} =10V, f=1MHz	-	-	10	рF

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TYPICAL CHARACTERISTICS

T_A=25°C, unless otherwise specified

Figure 1. V_{CE(sat)} vs. I_C

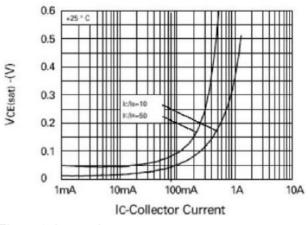
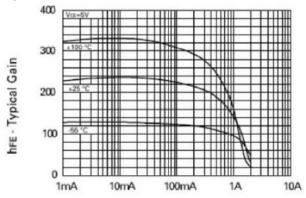


Figure 3. hFE vs. Ic



IC-Collector Current

Figure 5. $V_{\text{BE(on)}}$ vs. I_{C}

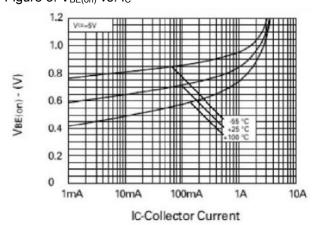


Figure 2. $V_{\text{CE(sat)}}$ vs. I_{C}

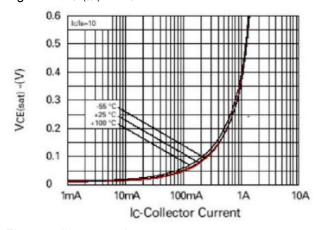
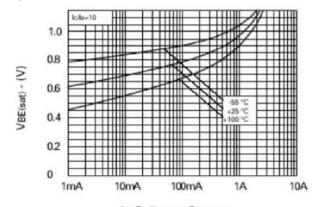
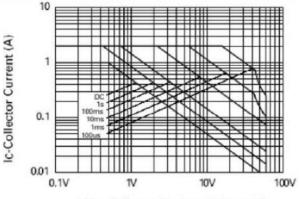


Figure 4. VBE(sat) vs. Ic



IC-Collector Current

Figure 6. Safe Operating Area

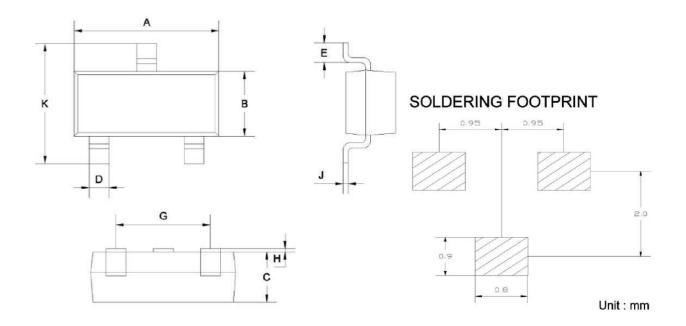


VCE - Collector Emitter Voltage (V)

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PACKAGE INFORMATION

Dimension in SOT-23 (Unit: mm)



Dim	Min	Max	
Α	2.85	2.95	
В	1.25	1.35	
С	1.0 Typical		
D	0.37	0.43	
E	0.35	0.48	
G	1.85	1.95	
Н	0.02	0.1	
J	0.1 Typical		
K	2.35	2.45	

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